

S/N 10/028643

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al.

Examiner: Long Pham

Serial No.: 10/028643

Group Art Unit: 2814

Filed: December 20, 2001

Docket: 1303.030US1

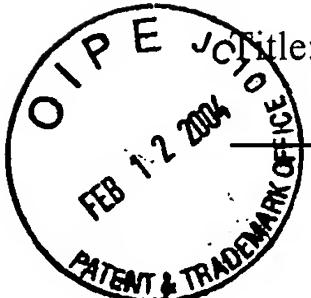
Title:

LOW-TEMPERATURE GROWN HIGH QUALITY ULTRA-THIN CoTiO₃
GATE DIELECTRICS

REQUEST TO REINTRODUCE WITHDRAWN CLAIMS

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

In the notice of allowability mailed on November 10, 2003, an Examiner's amendment was proposed canceling previously withdrawn claims 14-54. Applicant respectfully declines the Examiner's amendment, and instead requests that claims 14-54 be examined as species claims to allowed generic claim 1 pursuant to MPEP §809.04. Applicant notes that in a previous restriction requirement mailed on August 21, 2002, claim 1 was indicated as generic by the Examiner.



Conclusion

Applicant respectfully submits that pursuant to previously presented arguments, claims 14-54 are in condition for allowance in addition to previously allowed claims 1-13 and 55-67, and notification to that effect is earnestly requested. The Examiner is invited to telephone Applicant's attorney at (612) 373-6944 to facilitate prosecution of this application.

If necessary, please charge any additional fees or credit overpayment to Deposit Account No. 19-0743.

Respectfully submitted,

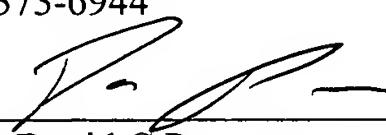
KIE Y. AHN ET AL.

By their Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
P.O. Box 2938
Minneapolis, MN 55402
(612) 373-6944

Date 2-10-04

By

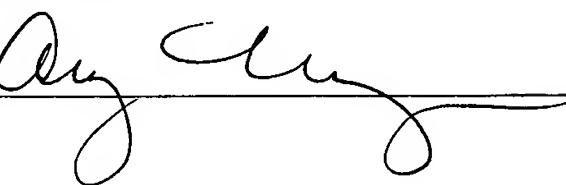

David C Peterson
Reg. No. 47,857

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on this 10th day of February, 2004.

Name

Amy Moriarty

Signature

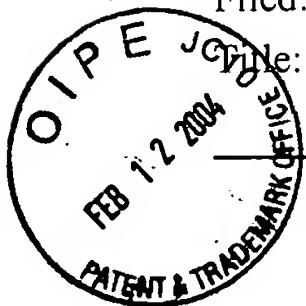


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Applicant: Kie Y. Ahn et al. Examiner: Long Pham
Serial No.: 10/028643 Group Art Unit: 2814
Filed: December 20, 2001 Docket: 1303.030US1
Title: LOW-TEMPERATURE GROWN HIGH QUALITY ULTRA-THIN COTIO3
GATE DIELECTRICS



COMMUNICATION CONCERNING RELATED APPLICATION(S)

MS RCE
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

<u>Serial/Patent No.</u>	<u>Filing Date</u>	<u>Attorney Docket</u>	<u>Title</u>
09/944981	August 30, 2001	1303.021US1	CRYSTALLINE OR AMOPHOUS MEDIUM-K GATE OXIDES, Y2O3 AND Gd2O3
09/945535	August 30, 2001	1303.026US1	HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE ZrO ₂
10/052983	January 17, 2002	1303.031US1	HIGHLY RELIABLE AMORPHOUS HIGH-k GATE DIELECTRIC ZrO _x N _y
10/027315	December 20, 2001	1303.033US1	LOW-TEMPERATURE GROWN HIGH-QUALITY ULTRA-THIN PRASEODYMIUM GATE DIELECTRICS
10/099194	March 13, 2002	1303.044US1	EVAPORATION OF Y-Si-O FILMS FOR MEDIUM-k DIELETRICS
10/081439	February 20, 2002	1303.046US1	EVAPORATED LaAlO ₃ FILMS FOR GATE DIELECTRICS
10/137499	May 2, 2002	1303.050US1	ATOMIC LAYER-DEPOSITED LaAlO ₃ FILMS FOR GATE DIELETRICS
10/163481	June 5, 2002	1303.056US1	ATOMIC LAYER-DEPOSITED HfAlO ₃ FILMS FOR GATE DIELECTRICS

COMMUNICATION CONCERNING RELATED APPLICATIONS**Page 2**

Serial Number: 10/028643

Dkt: 1303.030US1

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Title: LOW-TEMPERATURE GROWN HIGH QUALITY ULTRA-THIN COTIO₃ GATE DIELECTRICS

10/163686	June 5, 2002	1303.059US1	Pr ₂ O ₃ -BASED La-oxide GATE DIELECTRICS
10/209581	July 30, 2002	1303.061US1	ATOMIC LAYER DEPOSITED NANOLAMINATES OF HfO ₂ /ZrO ₂ FILMS AS GATE DIELECTRICS
10/219870	August 15, 2002	1303.069US1	LANTHANIDE DOPED TiO _x DIELECTRIC FILMS BY PLASMA OXIDATION
10/219878	August 15, 2002	1303.070US1	LANTHANIDE DOPED TiO _x DIELECTRIC FILMS
10/229903	August 28, 2002	1303.078US1	ATOMIC LAYER DEPOSITED HfSiON DIELECTRIC FILMS
10/233309	August 29, 2002	1303.079US1	ATOMIC LAYER DEPOSITED LANTHANIDE DOPED TiO _x DIELECTRIC FILMS
10/309583	December 4, 2002	1303.082US1	ATOMIC LAYER DEPOSITED ZR-SN-Ti-O FILMS USING TiI ₄
10/309935	December 4, 2002	1303.083US1	ATOMIC LAYER DEPOSITED Zr-Sn-Ti-O FILMS
10/379470	March 4, 2003	1303.090US1	ATOMIC LAYER DEPOSITED DIELECTRIC LAYERS
10/403734	March 31, 2003	1303.092US1	ATOMIC LAYER DEPOSITED ZrAl _x O _y DIELECTRIC LAYERS
10/420307	April 22, 2003	1303.097US1	ATOMIC LAYER DEPOSITED ZrTiO ₄ FILMS
10/602323	June 24, 2003	1303.101US1	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRIC LAYERS

COMMUNICATION CONCERNING RELATED APPLICATIONS

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Page 3

Dkt: 1303.030US1

10/602315	June 24, 2003	1303.107US1	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRICS
09/779959	February 9, 2001		
09/838335	April 20, 2001		
09/881408	June 13, 2001		
09/908/767	July 18, 2001		
10/765619	January 27, 2004	1303.033US2	LOW-TEMPERATURE GROWN HIGH- QUALITY ULTRA-THIN PRASEODYMIUM GATE DIELECTRICS
Unknown	January 30, 2004	1303.033US3	LOW-TEMPERATURE GROWN HIGH- QUALITY ULTRA-THIN PRASEODYMIUM GATE DIELECTRICS

Respectfully submitted,

KIE Y. AHN ET AL.

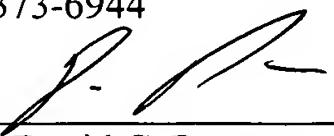
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Amy Moriarty
Name


Signature